TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

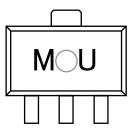
MT3S20P

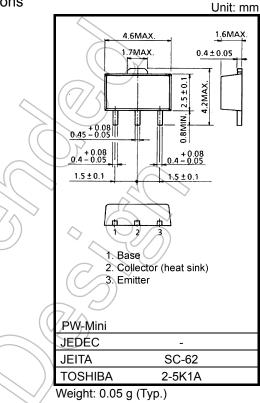
VHF-UHF Band Low-Noise, Low-Distortion Amplifier Applications

FEATURES

- Low Noise Figure: NF=1.45dB (typ.) (@f=1GHz)
- High Gain: |S21e|²=11dB (typ.) (@f=1GHz)

Marking





Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	VCBO	20	$\langle \mathbf{x} \rangle$
Collector-emitter voltage	VCEO	12	\rightarrow
Emitter-base voltage	VEBO	1.5	V
Collector current		80	mA
Base current	IB	10	mA
Collector power dissipation	PC	400	mW
Collector power dissipation	P _C (Note1)	1.8	W
Junction temperature	ŢĮ (150	°C
Storage temperature range	Tstg	-55 to 150	°C

Note 1 : The device is mounted on a ceramic board (25mm X 25mm X 0.8 mm (t))

Note.2 : Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Microwave Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Transition frequency	f _T	V _{CE} = 5V, I _C = 30mA	5	7	_	GHz
Insertion gain	S21e ² (1)	V _{CE} = 5V, I _C = 50mA, f = 500MHz	_	16.5	_	dB
	S21e ² (2)	V _{CE} = 5V, I _C = 50mA, f = 1GHz	9	11	_	
Noise figure	NF	V _{CE} = 5V, I _C = 20mA, f = 1GHz	Â	1.45	2	dB
3 rd order intermodulation distortion output intercept point	OIP3	V _{CE} = 5V, I _C = 50mA, f = 500MHz, ⊿f=1MHz	27.5	31.5	_	dBmW

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = 10V, I _E = 0		4	0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 1V, I _C = 0		4	0.5	μA
DC current gain	hFE	V _{CE} = 5V, I _C = 50mA	100	150	200	-
Reverse transfer capacitance	C _{re}	$V_{CB} = 5V$, $I_E = 0$, f = 1MHz (Note3)	\sim	0.85	/1.1	pF

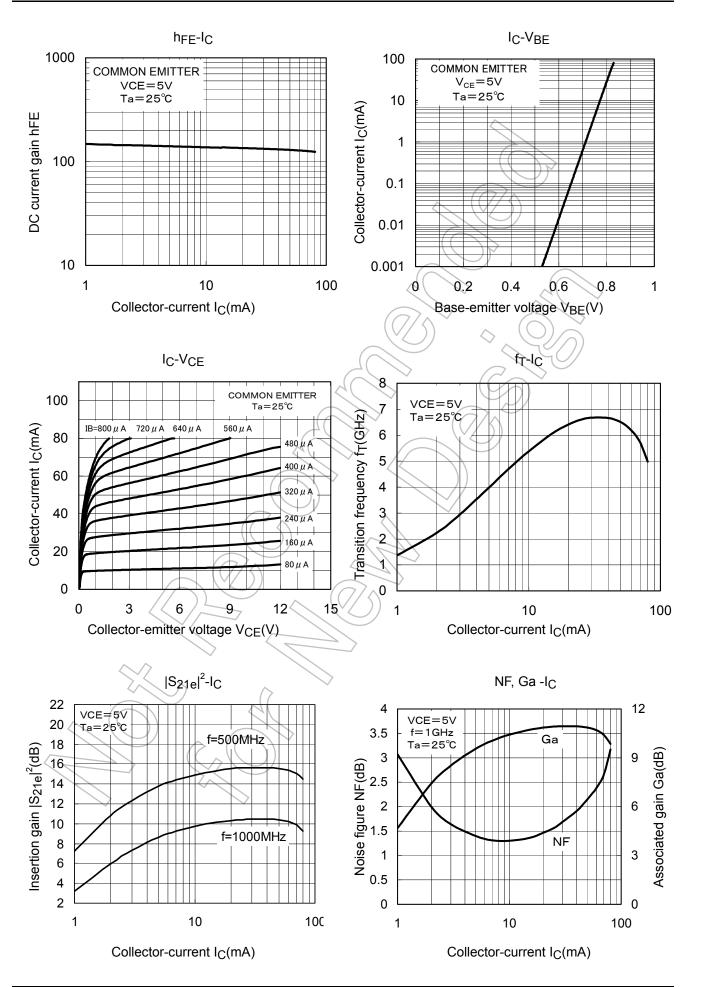
Note.3 : Cre is measured using a 3-terminal method with capacitance bridge.

Caution:

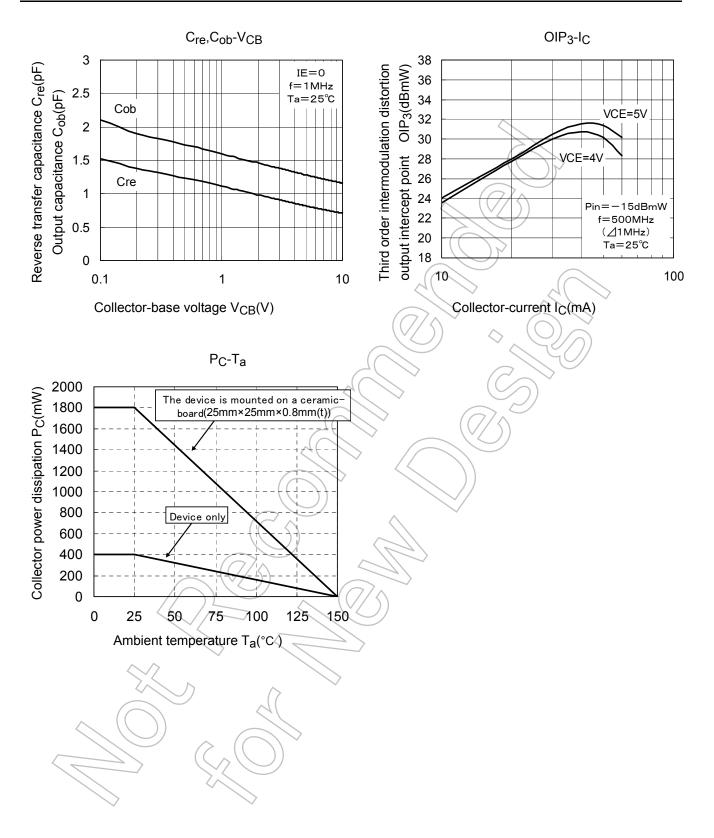
This device is sensitive to electrostatic discharge.

Please make enough tool and equipment earthed when you handle.

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